FMN1 IMN11 UMP1N
FMP1 IMP11 UMN11N
IMN10 UMN1N UMP11N

Diode, array, high speed switching, surface mount

In these single packages, there are three or four diodes as shown in the circuit diagrams.

Features

- available in SMD5 (FMT), UMD5 (UM5), SMD6 (IMD), and UMD6 (UM6) packages
- parts are marked as follows:

FMN1 = N1	UMN1N = N1
FMP1 = P1	UMP1N = P1
IMN10 = N10	UMN11N = N11
IMN11 = N11	UMP11N = P11
IMP11 = P11	

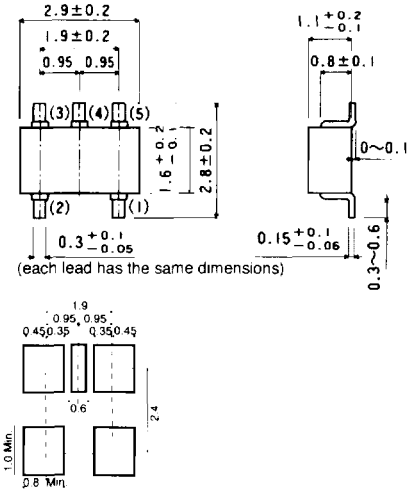
- suitable for automatic mounting on printed circuit board
- all diodes in the chip have similar characteristics

Applications

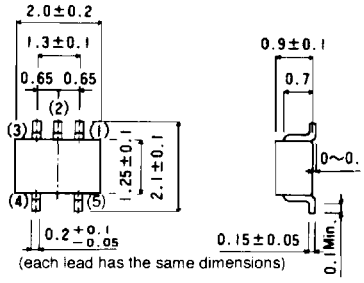
- high speed switching

Dimensions (Units : mm)

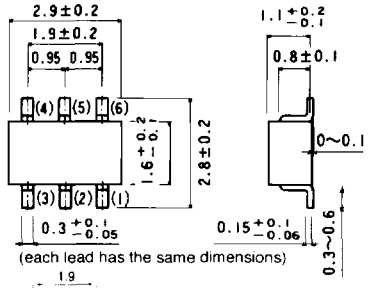
FMN1, FMP1
(SMD5)



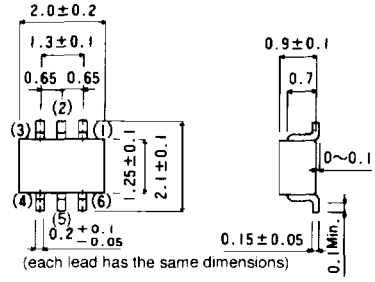
UMN1N, UMP1N (UMD5)

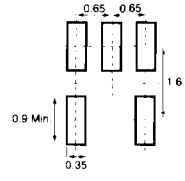


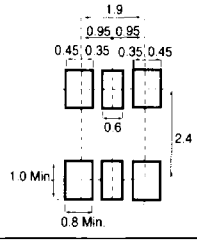
IMN10, IMN11, IMP11 (SMD6)

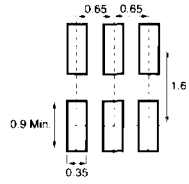


UMN11N, UMP11N (UMD6)



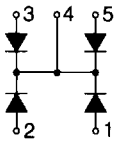




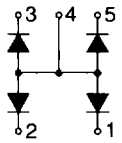


Equivalent circuits

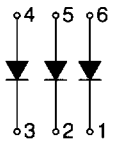
UMN1N



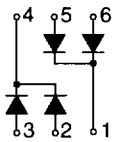
FMP1



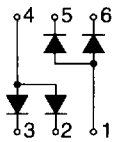
IMN10



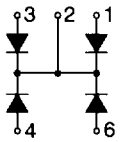
IMN11



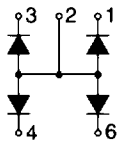
IMP11



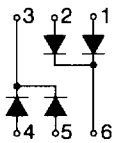
FMN1



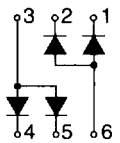
UMP1N



UMN11N



UMP11N



Absolute maximum ratings (T_a = 25°C)

Part no.	Peak reverse voltage	DC reverse voltage	Peak forward current	Mean rectifying current	Surge current	Power dissipation	Junction temp.	Storage temp.
	V_{RM} (V)	V_R (V)	I_F (mA)	I_O (mA)	(1μs) I_{surge} (A)	(Total) P_d (mW)	T_j (°C)	T_{stg} (°C)
FMN1 UMN1N	80	80	80	25	0.25	80 150	150	−55 ~ + 150
FMP1 UMP1N	80	80	80	25	0.25	80 150	150	−55 ~ + 150
IMN10	80	80	300	100	4	300[1]	150	−55 ~ + 150
IMN11 UMN11N	80	80	300	100	4	300[1] 150	150	−55 ~ + 150
IMP11 UMP11N	80	80	300	100	4	300[1] 150	150	−55 ~ + 150

[1] Not to exceed 200 mW per element

Electrical characteristics (unless otherwise noted, T_a = 25°C)

Part no.	Forward voltage		Reverse current		Capacitance between terminals			Reverse recovery time			
	V_F (V) Max	I_F (mA)	I_B (μA) Max	V_R (V)	C_T(pF) max.	V_R (V)	f (MHz)	t_{rr} (ns) Max	V_R (V)	I_F (mA)	Ref
FMN1 UMN1N	0.9	5	0.1	70	3.5	6	1	4	6	5	Figure 8
FMP1 UMP1N	0.9	5	0.1	70	3.5	6	1	4	6	5	Figure 8
IMN10	1.2	100	0.1	70	3.5	6	1	4	6	5	Figure 8
IMN11 UMN11N	1.2	100	0.1	70	3.5	6	1	4	6	5	Figure 8
IMP11 UMP11N	1.2	100	0.1	70	3.5	6	1	4	6	5	Figure 8

Electrical characteristic curves

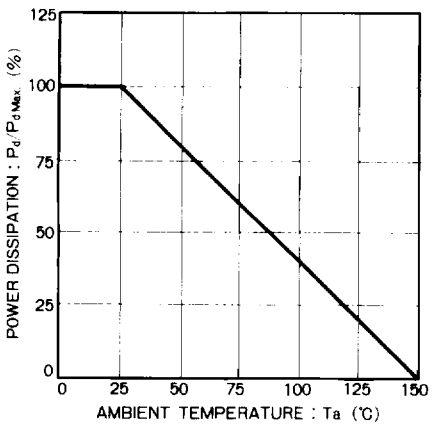


Figure 1

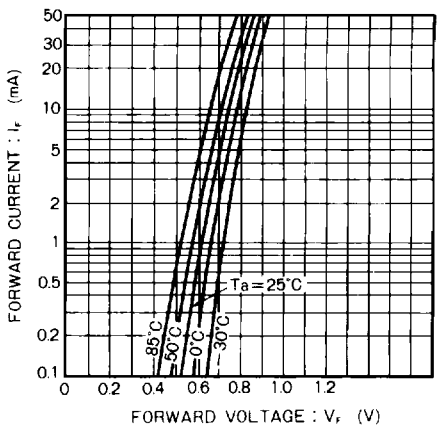


Figure 2

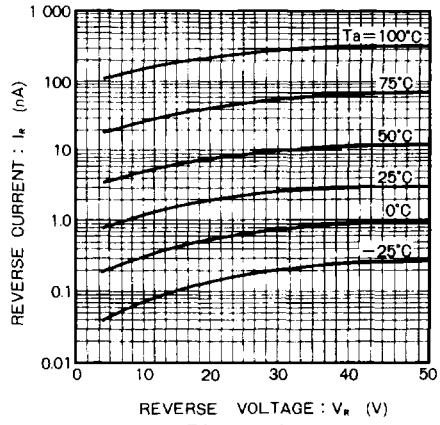


Figure 3

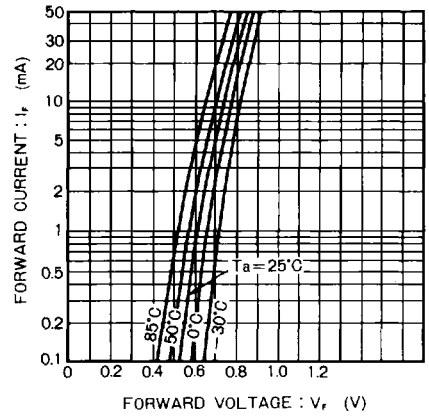


Figure 4

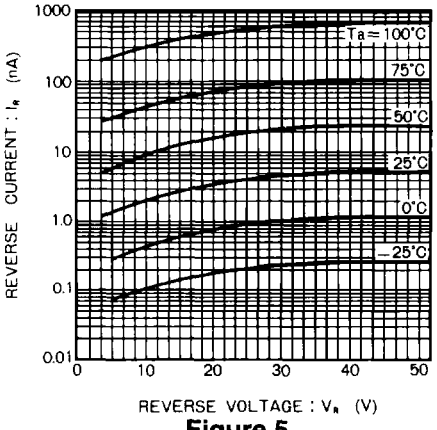


Figure 5

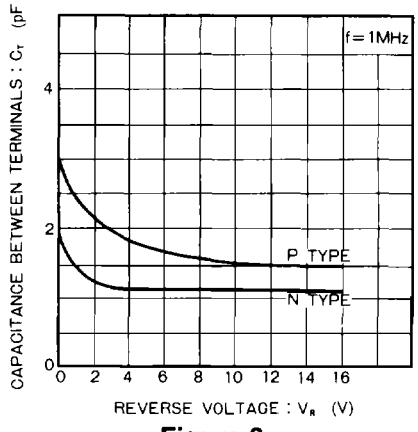


Figure 6

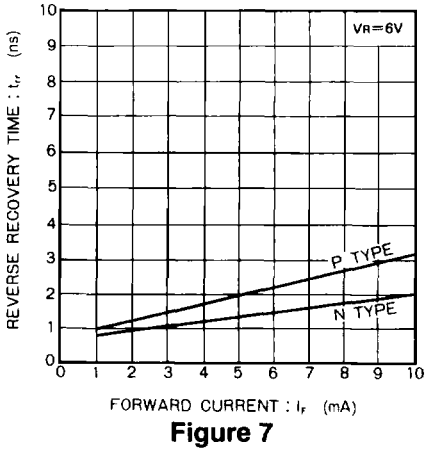
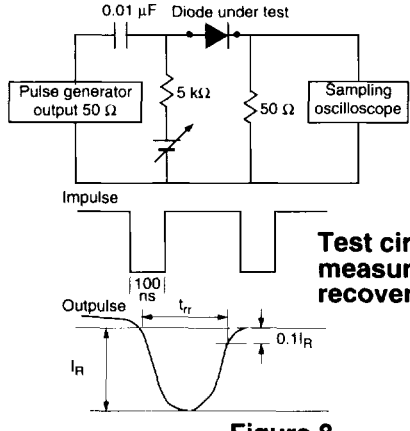


Figure 7



Test circuit for measuring reverse recovery time (t_{rr})

Figure 8